

Application No.: 10/791966

Case No.: 59522US003

Amendments to the Specification:

Please amend the specification as follows:

On p. 19, please replace the paragraph that begins on line 20 with the word "The" and ends on line 27 with the word "step" with the following amended paragraph:

-- "The well may be of any given shape including the truncated cone (frustum) shown in Fig. 5a or the channel shown in Fig. 5b, and have a depth that is up to [[75%]] 0.75% of the thickness of the original dielectric film. The conductive bump(s) may be of any shape including cylinders, truncated cones, polyhedrons, or combinations thereof. The height of the bumps will generally extend to the plane created by the unetched surface of the dielectric film. Additional copper may be plated to slightly increase the bump height and to form a cap on the bump. Alternatively, the height of the bumps may be reduced by performing a second metal etch step."--

On p. 20, please replace the paragraph that begins on line 13 with the word "Subsequently" and ends on line 20 with the word "etched" with the following amended paragraph:

-- "Subsequently, photoresist such as those available under the trade name SF320 or SF310 from MacDermid is laminated on the second (unmetallized) side of the polyimide film. The photoresist is patterned to define via openings by exposure to ultraviolet (UV) light through a phototool or mask, then developed with a [[75%]] 0.75% aqueous solution of sodium carbonate to obtain the desired image of the via pattern. Vias are formed by chemically etching the polyimide film from its second side using 35-55% KOH solution heated to a temperature of 70-95°C. The first flash copper layer serves as an etch stop for the chemical etching of the vias. The photoresist layer is removed after the vias are etched." --

On p. 20, please replace the paragraph that begins on line 28 with the word "Photoresist" and ends on p. 21, line 6 with the word "μm" with the following amended paragraph:

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--"Photoresist is laminated to the second flash copper layer and patterned to define circuitry (circuit traces or leads, bond pads and the like) and via entrances by exposure to UV light through a phototool or mask, then developed with [[75%]] 0.75% aqueous solution of sodium carbonate to obtain a desired image of circuitry pattern. Additional copper is then electroplated onto the second flash copper layer to form the final circuit leads and copper plugged vias to thicknesses of about 20-40 μm ."--

Support for these amendments are provided in the specification, e.g., at p. 13, lines 3-8.